

MOSFET – N-Channel, Logic Level, Enhancement Mode

FDN357N

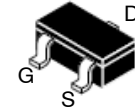
V _{DSS}	R _{DS(ON)} MAX	I _D MAX
30 V	0.09 Ω @ 4.5 V	1.9 A
	0.06 Ω @ 10 V	

General Description

SUPERSOT™ –3 N-Channel logic level enhancement mode power field effect transistors are produced using onsemi’s proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage applications in notebook computers, portable phones, PCMCIA cards, and other battery powered circuits where fast switching, and low in-line power loss are needed in a very small outline surface mount package.

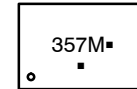
Features

- 1.9 A, 30 V
 - ♦ R_{DS(ON)} = 0.09 Ω @ V_{GS} = 4.5 V
 - ♦ R_{DS(ON)} = 0.06 Ω @ V_{GS} = 10 V
- Industry Standard Outline SOT–23 Surface Mount Package Using Proprietary SUPERSOT–3 Design for Superior Thermal and Electrical Capabilities
- High Density Cell Design for Extremely Low R_{DS(ON)}
- Exceptional On-Resistance and Maximum DC Current Capability
- This Device is Pb-Free and is RoHS Compliant



SOT-23/SUPERSOT™ –23, 3 LEAD, 1.4x2.9 CASE 527AG

MARKING DIAGRAM



- 357 = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C, unless otherwise noted)

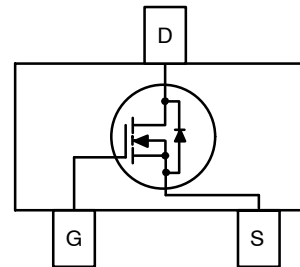
Symbol	Parameter	Value	Unit
V _{DSS}	Drain-Source Voltage	30	V
V _{GSS}	Gate-Source Voltage – Continuous	±20	V
I _D	Drain/Output Current	Continuous	1.9
		Pulsed	10
P _D	Maximum Power Dissipation	(Note 1a)	0.5
		(Note 1b)	0.46
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (T_A = 25°C, unless otherwise noted)

Symbol	Parameter	Max	Unit
R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1a)	250	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case (Note 1)	75	°C/W

PIN ASSIGNMENT



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

FDN357N

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	30	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	-	36	-	mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 24 V, V _{GS} = 0 V, T _J = 55°C	-	-	10	μA
I _{GSSF}	Gate - Body Leakage, Forward	V _{GS} = 20 V, V _{DS} = 0 V	-	-	100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	V _{GS} = -20 V, V _{DS} = 0 V	-	-	-100	nA

ON CHARACTERISTICS (Note 2)

V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	1	1.6	2	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	-	-3.6	-	mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 4.5 V, I _D = 1.9 A	-	0.081	0.09	Ω
		V _{GS} = 4.5 V, I _D = 1.9 A, T _J = 125°C	-	0.11	0.14	
		V _{GS} = 10 V, I _D = 2.2 A	-	0.053	0.06	
I _{D(on)}	On-State Drain Current	V _{GS} = 4.5 V, V _{DS} = 5 V	5	-	-	A
g _{FS}	Forward Transconductance	V _{DS} = 5 V, I _D = 1.9 A	-	5	-	S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	-	235	-	pF
C _{oss}	Output Capacitance		-	145	-	pF
C _{rss}	Reverse Transfer Capacitance		-	50	-	pF

SWITCHING CHARACTERISTICS (Note 2)

t _{D(on)}	Turn-On Delay Time	V _{DD} = 10 V, I _D = 1 A, V _{GS} = 10 V, R _{GEN} = 6 Ω	-	5	10	ns
t _r	Turn-On Rise Time		-	12	22	ns
t _{D(off)}	Turn-Off Delay Time		-	12	22	ns
t _f	Turn-Off Fall Time		-	3	8	ns
Q _g	Total Gate Charge	V _{DS} = 10 V, I _D = 1.9 A, V _{GS} = 5 V	-	4.2	5.9	nC
Q _{gs}	Gate-Source Charge		-	1.3	-	nC
Q _{gd}	Gate-Drain Charge		-	1.7	-	nC

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

I _S	Maximum Continuous Drain-Source Diode Forward Current		-	-	0.42	A
V _{SD}	Source-Drain Diode Forward Voltage	V _{GS} = 0 V, I _S = 0.42 A (Note 2)	-	0.71	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

- R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design while R_{θCA} is determined by the user's board design. Typical R_{θJA} using the board layouts shown below on 4.5" x 5" FR-4 PCB in a still air environment:



- a) 250°C/W when mounted on
a 0.02 in² pad of 2 oz Cu



- b) 270°C/W when mounted on
a 0.001 in² pad of 2 oz Cu

- Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

TYPICAL ELECTRICAL CHARACTERISTICS

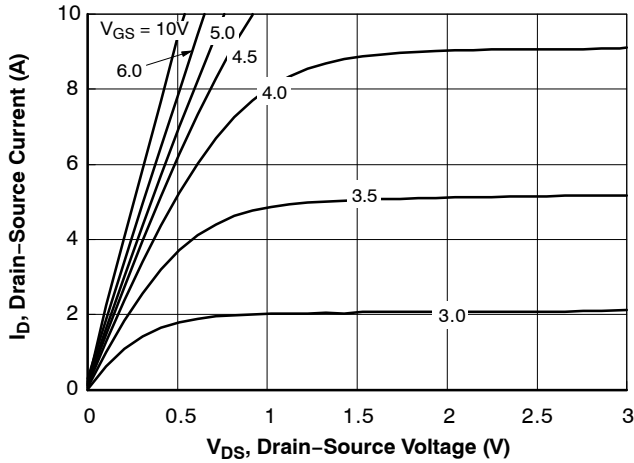


Figure 1. On Region Characteristics

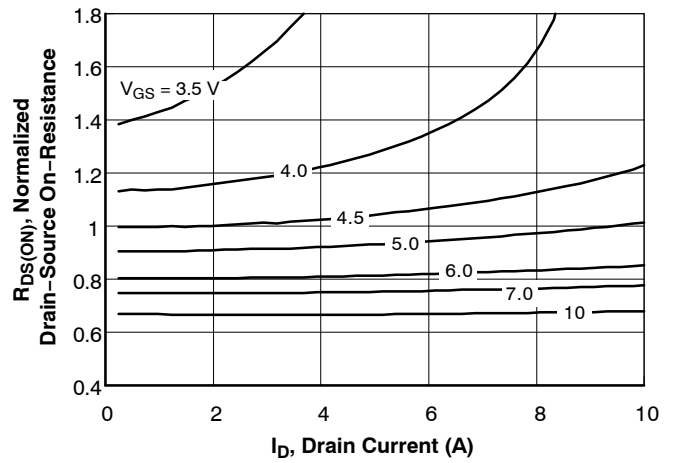


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

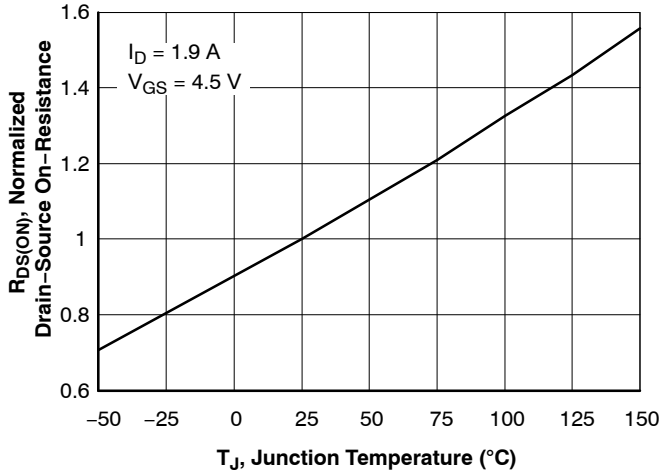


Figure 3. On-Resistance Variation with Temperature

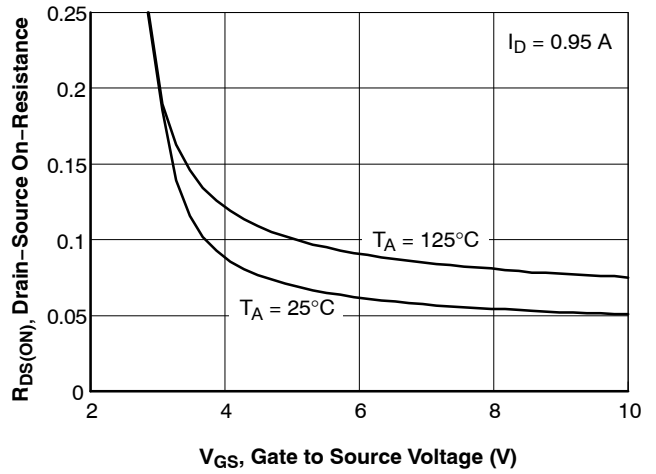


Figure 4. On-Resistance Variation with Gate to Source Voltage

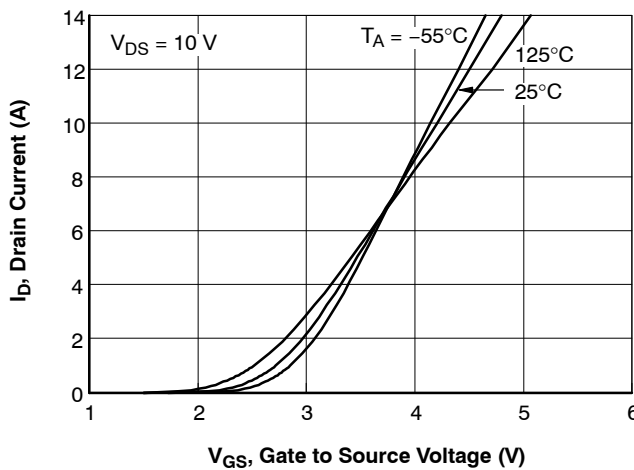


Figure 5. Transfer Characteristics

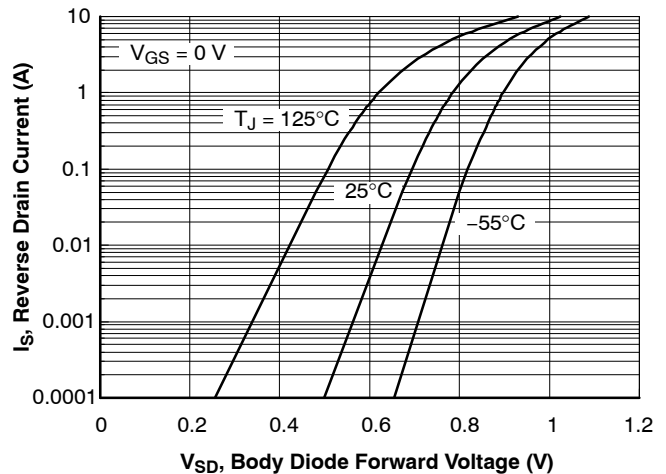


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

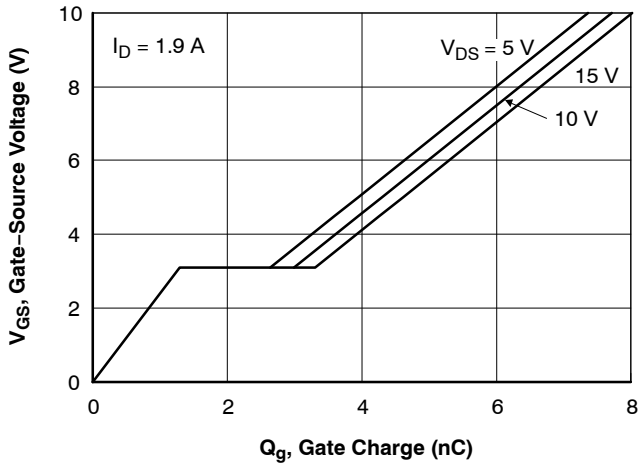


Figure 7. Gate Charge Characteristics

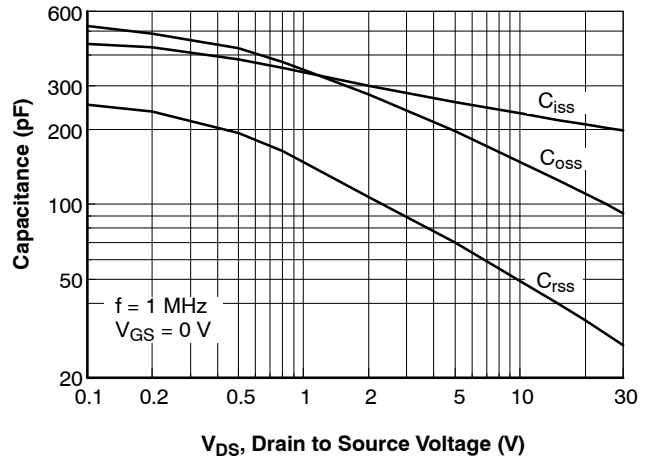


Figure 8. Capacitance Characteristics

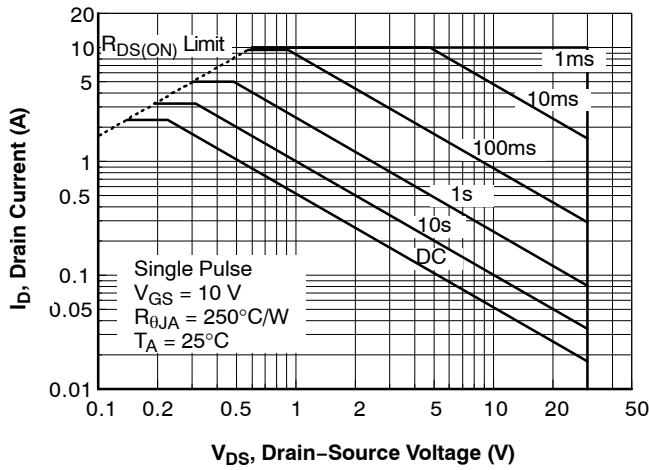


Figure 9. Maximum Safe Operating Area

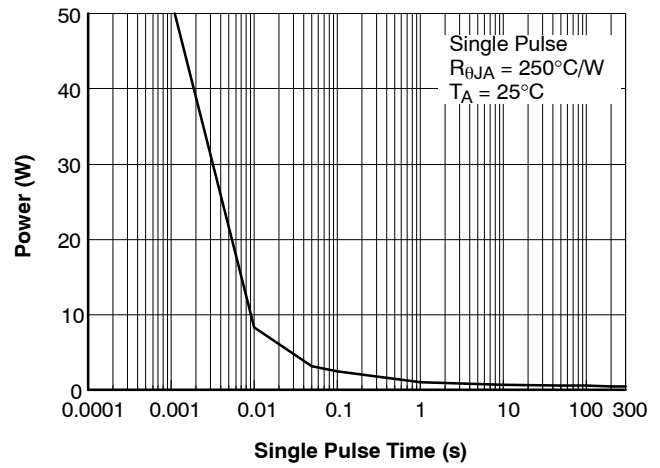


Figure 10. Single Pulse Maximum Power Dissipation

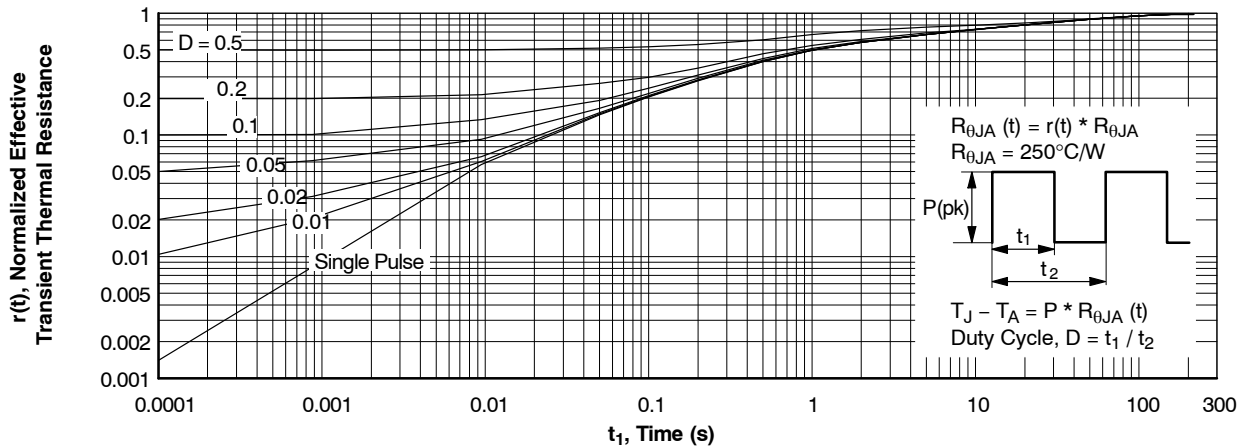


Figure 11. Transient Thermal Response Curve

NOTE: Thermal characterization performed using the conditions described in Note 1a. Transient thermal response will change depending on the circuit board design.

FDN357N

PACKAGE MARKING AND ORDERING INFORMATION

Device	Device Marking	Package	Shipping [†]
FDN357N	357	SOT-23/SUPERSOT-23, 3 LEAD, 1.4x2.9 (Pb-Free, Halide Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SOT-23/SUPERSOT™ -23, 3 LEAD, 1.4x2.9
CASE 527AG
ISSUE A

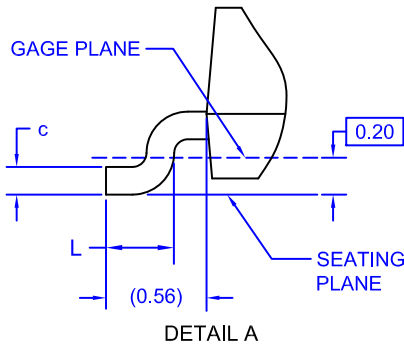
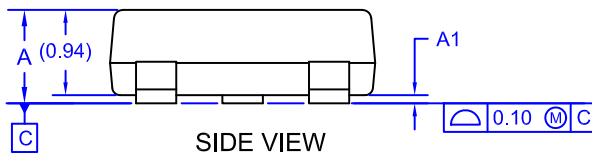
DATE 09 DEC 2019



NOTES: UNLESS OTHERWISE SPECIFIED

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.

DIM	MIN.	NOM.	MAX.
A	0.85	0.95	1.12
A1	0.00	0.05	0.10
b	0.370	0.435	0.508
c	0.085	0.150	0.180
D	2.80	2.92	3.04
E	2.31	2.51	2.71
E1	1.20	1.40	1.52
e	0.95 BSC		
e1	1.90 BSC		
L	0.33	0.38	0.43



*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



- XXX = Specific Device Code
- M = Month Code
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	SOT-23/SUPERSOT-23, 3 LEAD, 1.4X2.9	PAGE 1 OF 1

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